

ABSTRACT

A bond pad structure for an integrated circuit includes first and second active devices formed in a substrate, first and second buses above the first and second active devices, respectively, a bond pad above the first and second buses, first
5 interconnections between the first and second active devices and the bond pad, and second interconnections between the first and second active devices and the first and second buses, respectively. The first active device may be at least one PMOS transistor, and the second active device may be at least one NMOS transistor. A guard band region may be formed in the substrate.